

## S4D20120A S4D20120H S4D20120G 1200V SiC POWER SCHOTTKY RECTIFIERS

### Description

S4D20120A/S4D20120H/S4D20120G are SiC Schottky rectifiers packaged in TO-220AC(TO-220-2)/TO-247AC(TO-247-2)/D2PAK(TO-263-2) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D20120A/S4D20120H/S4D20120G are ideal for energy sensitive, high frequency applications in challenging environments.

### Features

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

### Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	1200	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>c</sub> =150°C, rectangular wave form	20	A
Repetitive Peak Forward Surge Current	I <sub>FRM</sub>	10 ms, Half Sine pulse , T <sub>J</sub> =25°C	91	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	10ms, Half Sine pulse, T <sub>J</sub> =25°C	162	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 20A, Pulse, T <sub>J</sub> = 25 °C	1.5	1.8	V
	V <sub>F2</sub>	@ 20A, Pulse, T <sub>J</sub> = 175 °C	2.2	3.0	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	35	200	uA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 175 °C	65	400	uA
Junction Capacitance	C <sub>T</sub>	VR=0V, Tj=25°C, f=1MHz	1620	-	pF

\* Pulse width < 300 μs, duty cycle < 2%

### Thermal-Mechanical Specifications:

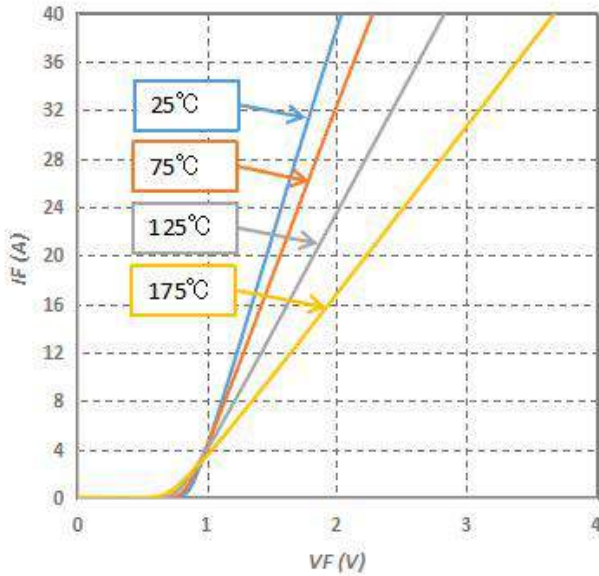
Characteristics	Symbol	S4D20120A	S4D20120H	S4D20120G	Units
Junction Temperature	T <sub>J</sub>	-55 to +175			°C
Storage Temperature	T <sub>stg</sub>	-55 to +175			°C
Maximum Thermal Resistance Junction to Case	R <sub>qJC</sub>	1.7	0.61	1.65	°C/W

### Ordering Information

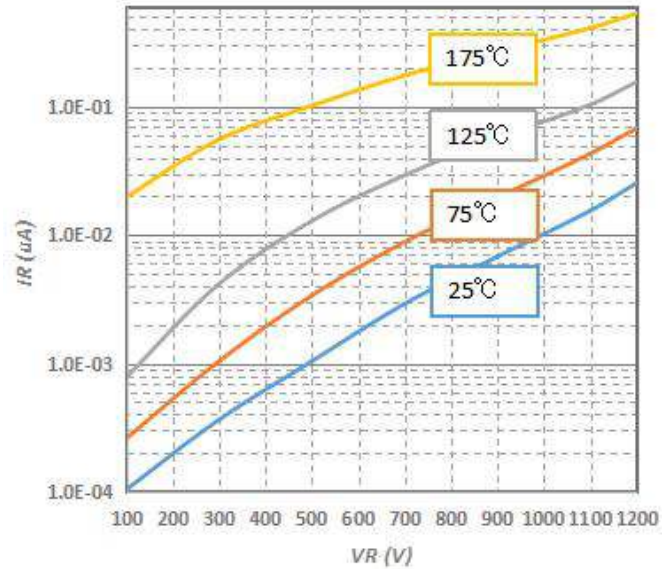
Device	Package	Shipping
S4D20120A	TO-220AC(TO-220-2)	50pcs / tube
S4D20120H	TO-247AC(TO-247-2)	25pcs / tube
S4D20120G	D2PAK(TO-263-2)	800pcs/reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

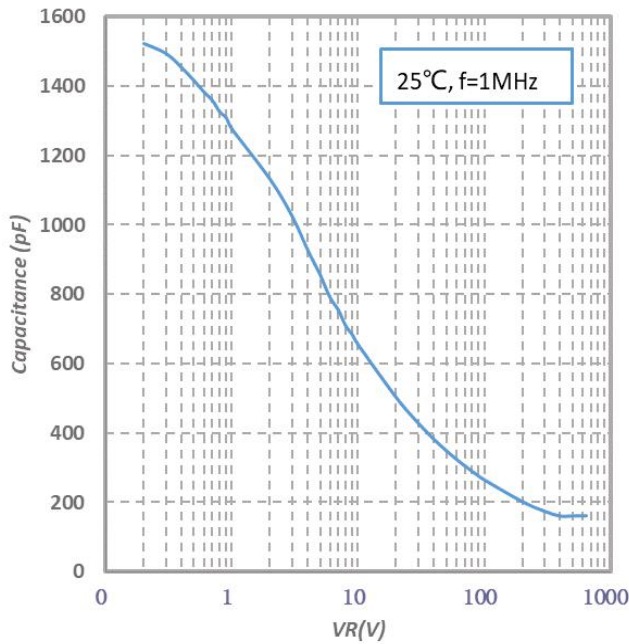
**Ratings and Characteristics Curves**



**Fig.1-Typical Forward Voltage Characteristics**

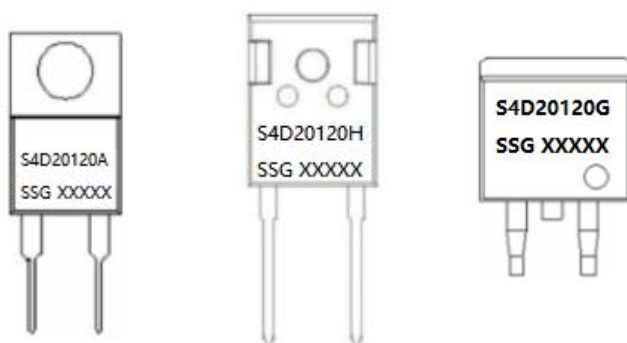


**Fig.2-Typical Reverse Characteristics**



**Fig.3-Capacitance vs. Reverse Voltage**

## Marking Diagram

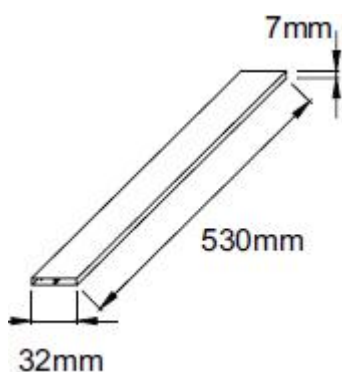


Where XXXXX is YYWWL

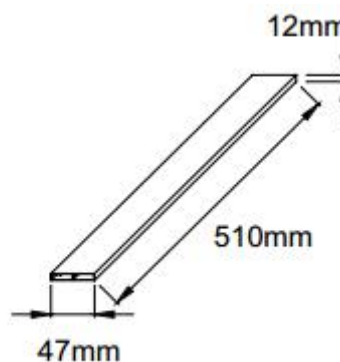
S4D = Device Type  
A/H/G = Package type  
20 = Forward Current (20A)  
120 = Reverse Voltage (1200V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

## Tube Specification

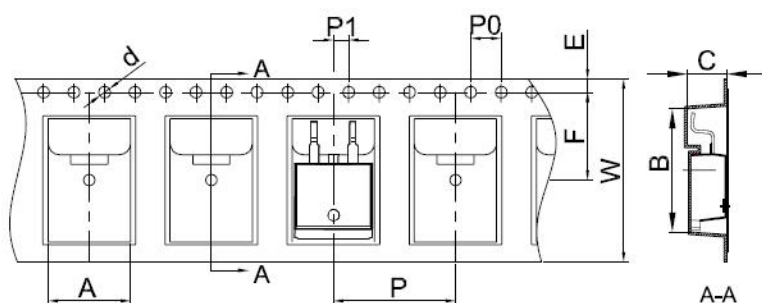


TO-220AC(TO-220-2)



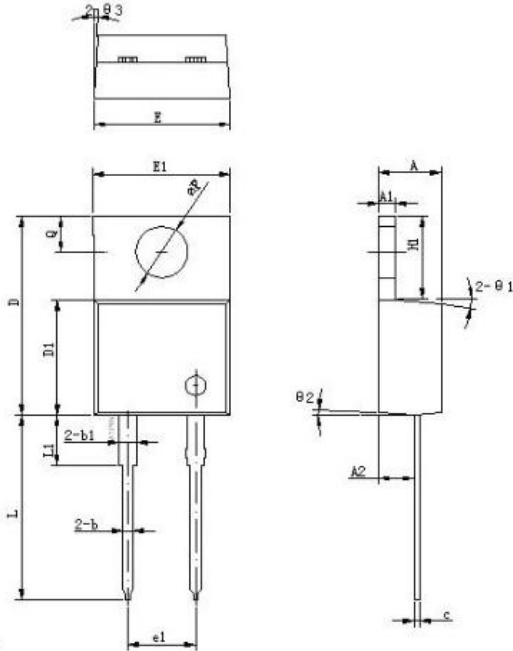
TO-247AC(TO-247-2)

## Carrier Tape & Reel Specification D2PAK(TO-263-2)



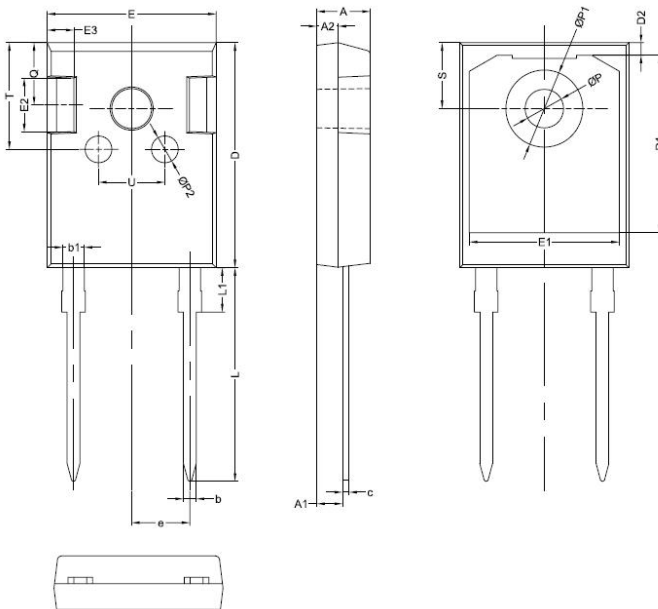
SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

**Mechanical Dimensions TO-220AC(TO-220-2)**



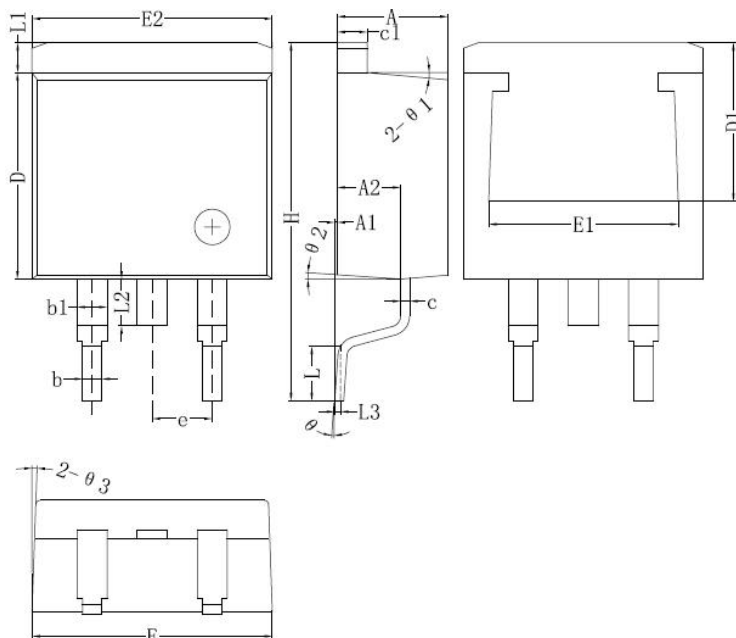
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.64	14.94	15.24
D1	8.55	8.70	8.90
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1		5.08	
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1		3.80	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

**Mechanical Dimensions TO-247AC(TO-247-2)**



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

**Mechanical Dimensions D<sup>2</sup>PAK(TO-263-2)**



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
$\theta$	0	-	8°
$\theta_1$		5°	
$\theta_2$		4°	
$\theta_3$		4°	

**Technical Data**  
**Data Sheet N2367, REV.B**



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